

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of depositing a patterned film of an organic material on a substrate, comprising:
 - mixing vapor of an organic material for deposition with a carrier gas;
 - introducing the carrier gas carrying the organic material for deposition into a nozzle;
 - ejecting the carrier gas carrying the organic material from the nozzle at a flow velocity that is at least 10% of the thermal velocity of the carrier gas, such that the organic material introduced with the carrier gas into the nozzle is deposited onto a substrate, separated from the nozzle, forming a plurality of separate films of the organic material on the substrate;
 - wherein a region between the nozzle and the substrate surrounding the carrier gas has a dynamic pressure of at least 1 Torr ~~greater than the background pressure.~~
2. (Original) The method of claim 1, wherein the dynamic pressure is at least 10 Torr.
3. (Previously Presented) The method of claim 2, wherein a background pressure of at least 5 Torr is provided.

4. (Original) The method of claim 2, further comprising: ejecting a guard flow from the nozzle.
5. (Previously Presented) The method of claim 1, wherein a background pressure of about 760 Torr is provided, and the background pressure is the ambient atmosphere.
6. (Original) The method of claim 2, wherein the dynamic pressure of at least 10 Torr is affected by a guard flow ejected from the nozzle.
7. (Previously Presented) The method of claim 6, wherein the method is performed in a vacuum chamber at base pressure, thereby providing a background pressure of less than about 0.1 Torr.
8. (Original) The method of claim 7, wherein the molecular weight of the organic material is greater than the molecular weight of the carrier gas.
9. (Original) The method of claim 6, wherein the guard flow comprises a first gas, the carrier gas comprises a second gas, and the molecular weight of the first gas is greater than the molecular weight of the second gas.

10. (Original) The method of claim 1, wherein the dynamic pressure is at least about 760 Torr.

11. (Previously Presented) A method of depositing a patterned film of an organic material on a substrate, comprising:

 mixing vapor of an organic material for deposition with a carrier gas;
 introducing the carrier gas carrying the organic material for deposition into a nozzle;
 ejecting the carrier gas carrying the organic material from the nozzle at a flow velocity that is at least 10% of the thermal velocity of the carrier gas, such that the organic material introduced with the carrier gas into the nozzle is deposited onto a substrate, separated from the nozzle, forming a plurality of separate films of the organic material on the substrate; and
 providing a guard flow around the carrier gas.

12. (Original) The method of claim 11, wherein the method is performed with a background pressure of at least about 760 Torr.

13. (Original) The method of claim 11, wherein the method is performed in a glove-box without the use of a vacuum apparatus.

14. (Previously Presented) The method of claim 1, wherein a background pressure of at least about 10^{-3} Torr is provided.

15. (Original) The method of claim 14, wherein the background pressure is at least 0.1 Torr.

16. (Original) The method of claim 15, wherein the background pressure is at least 1 Torr.

17. (Original) The method of claim 16, wherein the background pressure is at least 10 Torr.

18. (Previously Presented) The method of claim 17, wherein the background pressure is at least about 760 Torr.

19. (Original) The method of claim 18, wherein the background pressure of at least about 760 Torr is provided by a glove box without the use of a vacuum apparatus.

20. (Original) The method of claim 14, wherein the background pressure is achieved without the use of vacuum apparatus.

21-33. (Canceled).

34. (Previously Presented) The method of claim 1, wherein the dynamic pressure is not greater than about 2 times the background pressure.

35. (Previously Presented) The method of claim 1, wherein the dynamic pressure is not greater than about 10 times the background pressure.
36. (Previously Presented) The method of claim 1, wherein the plurality of films comprises a plurality of pixels.
37. (Previously Presented) The method of claim 11, wherein the plurality of films comprises a plurality of pixels.
38. (Previously Presented) The method of claim 1, wherein at least one of the nozzle diameter, the nozzle length, and nozzle-to-substrate separation is about equal to the gas mean free path length.
39. (Previously Presented) The method of claim 11, wherein at least one of the nozzle diameter, the nozzle length, and nozzle-to-substrate separation is about equal to the gas mean free path length.
40. (New) The method of claim 1, wherein the dynamic pressure is at least 0.5 Torr greater than the background pressure.